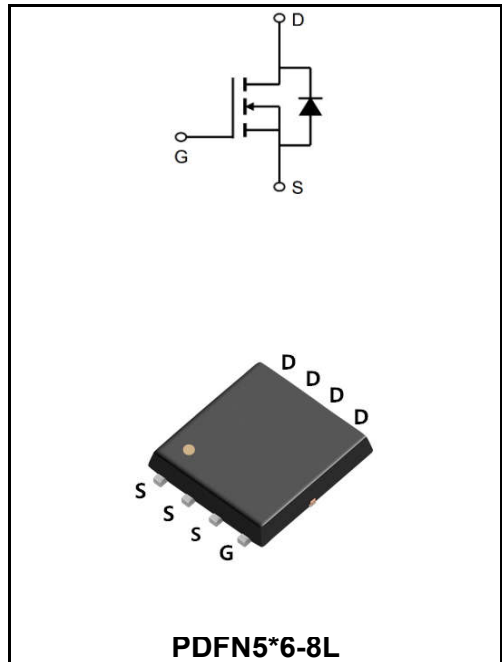


**30V N-CHANNEL ENHANCEMENT MODE MOSFET**

**MAIN CHARACTERISTICS**

<b>I<sub>D</sub></b>	150A
<b>V<sub>DSS</sub></b>	30V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=10V)</sub></b>	< 2mΩ (Type: 1.4 mΩ)



**Application**

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply



**Product Specification Classification**

Part Number	Package	Marking	Pack
YFW150N03NF	PDFN5*6-8L	YFW 150N03NF XXXXX	5000PCS/Tape

**Maximum Ratings at T<sub>c</sub>=25°C unless otherwise specified**

Characteristics	Symbols	Value	Units
Drain-Source Voltage	<b>V<sub>DS</sub></b>	30	<b>V</b>
Gate - Source Voltage	<b>V<sub>GS</sub></b>	±20	<b>V</b>
Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1.6</sup> @T <sub>c</sub> =25°C	<b>I<sub>D</sub></b>	150	<b>A</b>
Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1.6</sup> @T <sub>c</sub> =100°C	<b>I<sub>D</sub></b>	78	<b>A</b>
Pulsed Drain Current <sup>2</sup>	<b>I<sub>DM</sub></b>	500	<b>A</b>
Single Pulsed Avalanche Energy <sup>3</sup>	<b>E<sub>AS</sub></b>	240	<b>mJ</b>
Avalanche Current	<b>I<sub>AS</sub></b>	55	<b>A</b>
Total Power Dissipation <sup>4</sup> @T <sub>c</sub> =25°C	<b>P<sub>D</sub></b>	48	<b>W</b>
Total Power Dissipation <sup>4</sup> @T <sub>A</sub> =25°C	<b>P<sub>D</sub></b>	2.6	<b>W</b>
Storage Temperature Range	<b>T<sub>STG</sub></b>	-55 to +175	<b>°C</b>
Operating Junction Temperature Range	<b>T<sub>J</sub></b>	-55 to +175	<b>°C</b>
Thermal Resistance Junction-ambient <sup>1</sup>	<b>R<sub>θJA</sub></b>	62	<b>°C/W</b>
Thermal Resistance Junction-Ambient 1 (t ≤ 10s)	<b>R<sub>θJA</sub></b>	25	<b>°C/W</b>
Thermal Resistance, Junction - Case <sup>1</sup>	<b>R<sub>θJC</sub></b>	2.6	<b>°C/W</b>

**Maximum Ratings at Tc=25°C unless otherwise specified**

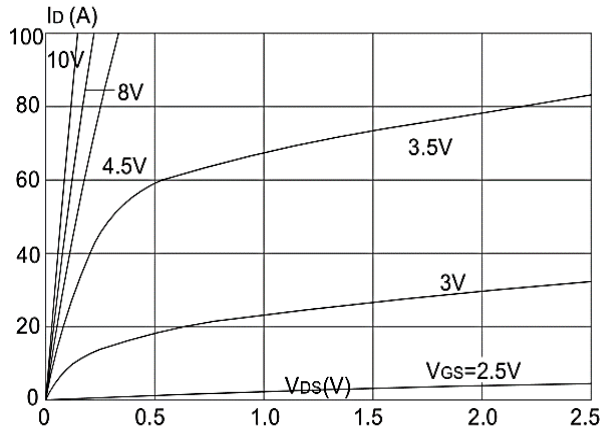
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	$BV_{DSS}$	30	33	-	V
BVDSS Temperature Coefficient	Reference to 25°C, $I_D=1mA$	$\Delta BV_{DSS}/\Delta T_J$		0.0213		V/°C
Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=30A$	$R_{DS(ON)}$	-	1.4	2.0	mΩ
	$V_{GS}=4.5V, I_D=20A$		-	2.3	3.2	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient		$\Delta V_{GS(th)}$	-	-5.73	-	mV/°C
Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ C$	$I_{DSS}$	-	-	1	μA
	$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ C$		-	-	5	
Gate -Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	$I_{GSS}$	-	-	±100	nA
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	$R_g$	-	1.4	-	Ω
Total Gate Charge(4.5V)	$V_{DS}=15V$ $V_{GS}=4.5V$ $I_D=30A$	$Q_g$	-	70	-	nC
Gate-Source Charge		$Q_{gs}$	-	12	-	
Gate-Drain Charge		$Q_{gd}$	-	17	-	
Turn-on delay time	$V_{DD}=15V$ $V_{GS}=10V$ $I_D=30A$ $R_G=3\Omega$	$t_{d(on)}$	-	10	-	ns
Rise Time		$T_r$	-	6.5	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	75	-	
Fall Time		$t_f$	-	18	-	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	$C_{iss}$	-	4930	-	pF
Output Capacitance		$C_{oss}$	-	682	-	
Reverse Transfer Capacitance		$C_{rss}$	-	566	-	
Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V, \text{Force Current}$	$I_S$	-	-	120	A
Pulsed Source Current <sup>2,5</sup>		$I_{SM}$	-	-	480	A
Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=30A, T_J=25^\circ C$	$V_{SD}$	-	-	1.2	V
Body Diode Reverse Recovery Charge	$I_F=20A, di/dt=100A/\mu s$	$Q_{rr}$	-	30	-	ns
Body Diode Reverse Recovery Time		$t_{rr}$	-	15	-	nC

Note :

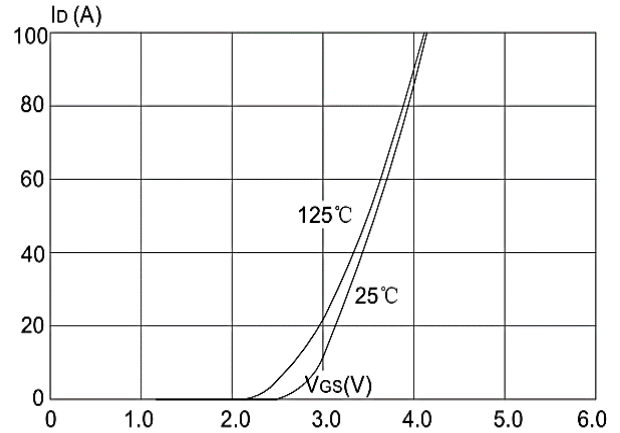
- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3、 The EAS data shows Max. rating . The test condition is  $V_{DD}=24V, V_{GS}=10V, L=0.1mH, I_{AS}=55A$
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation

**Ratings and Characteristic Curves**

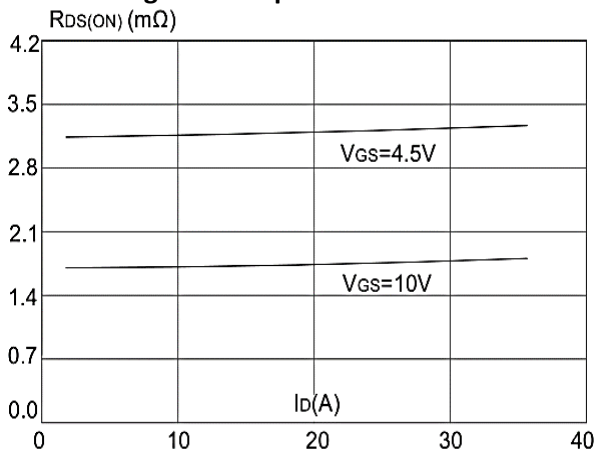
**Typical Characteristics**



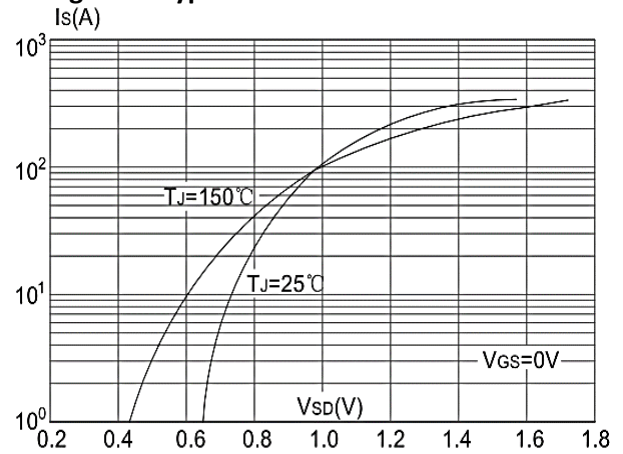
**Figure 1: Output Characteristics**



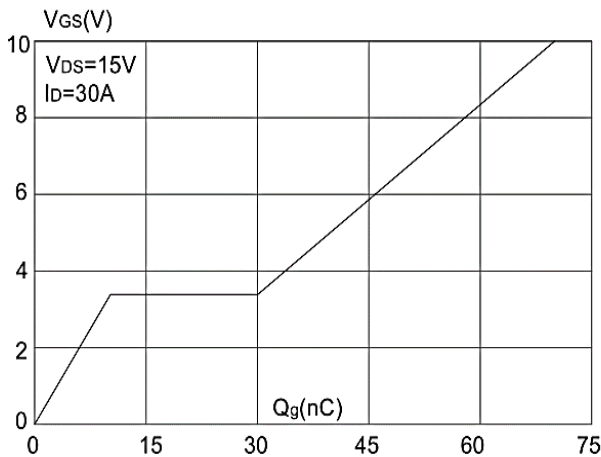
**Figure 2: Typical Transfer Characteristics**



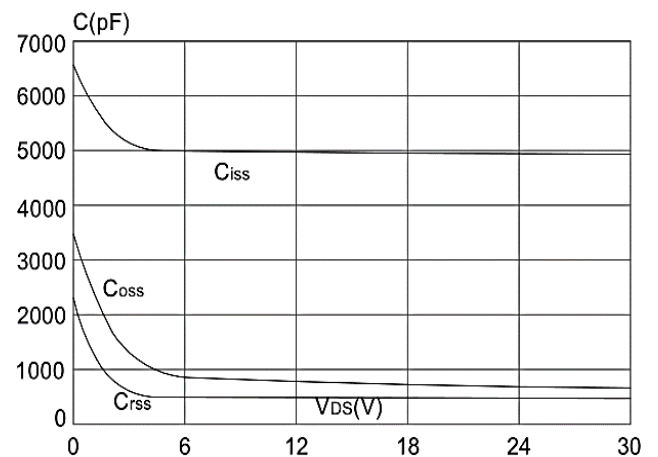
**Figure 3: On-resistance vs. Drain Current**



**Figure 4: Body Diode Characteristics**

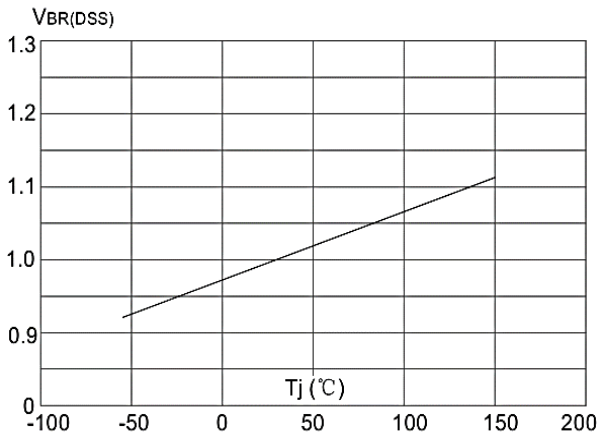


**Figure 5: Gate Charge Characteristics**

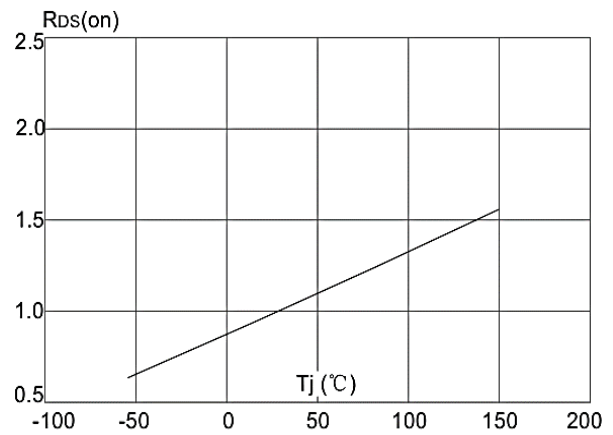


**Figure 6: Capacitance Characteristics**

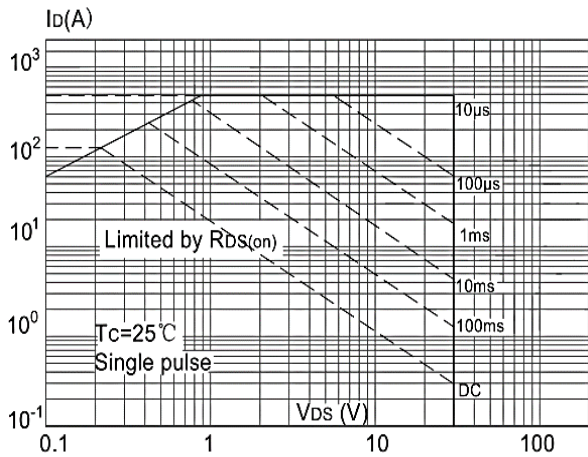
**Ratings and Characteristic Curves**



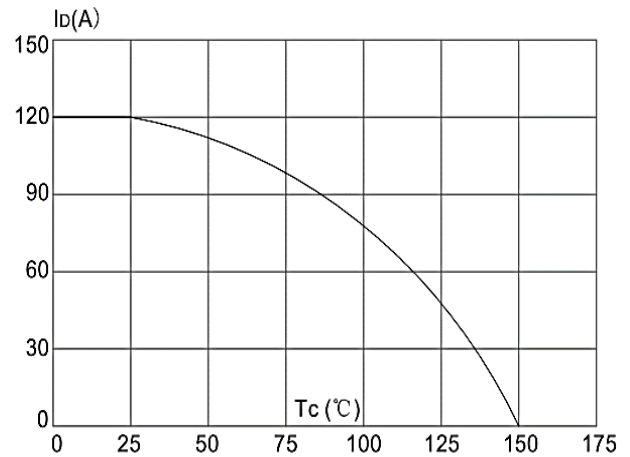
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



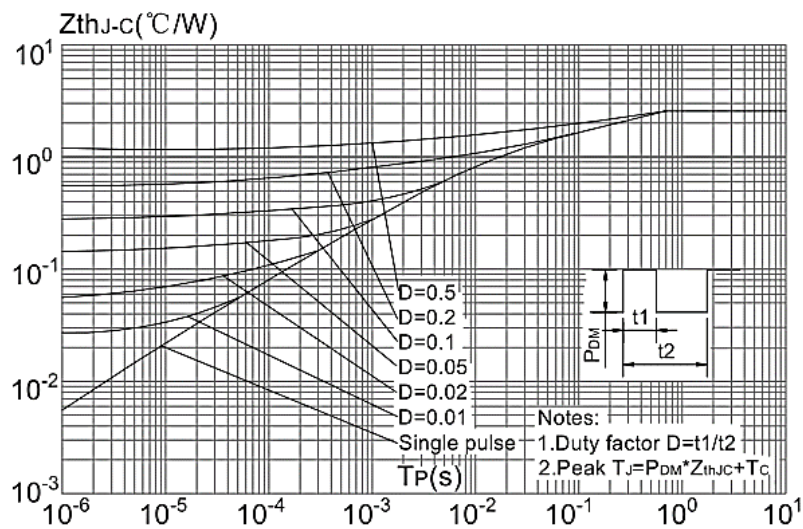
**Figure 8: Normalized on Resistance vs. Junction Temperature**



**Figure 9: Maximum Safe Operating Area vs. Case Temperature**

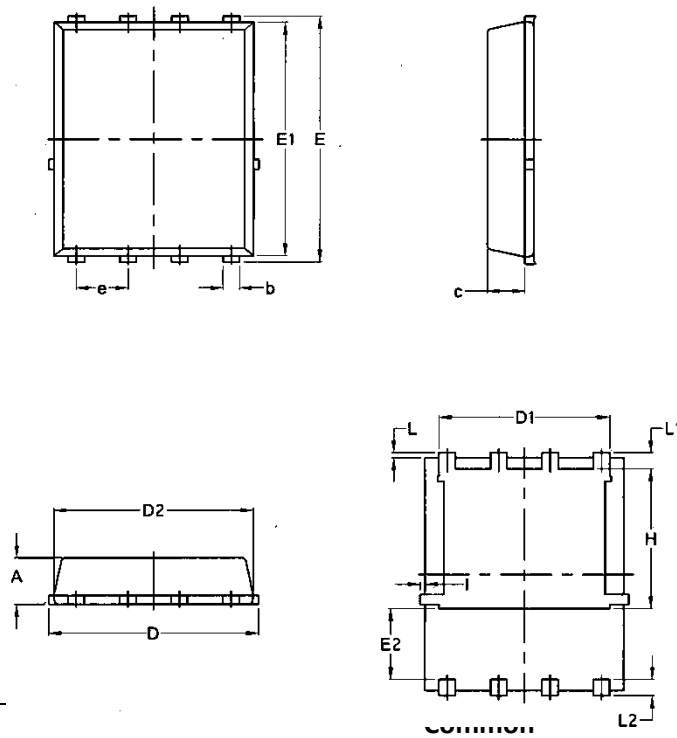


**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**



**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**PDFN5\*6-8L**



Symbol	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070